

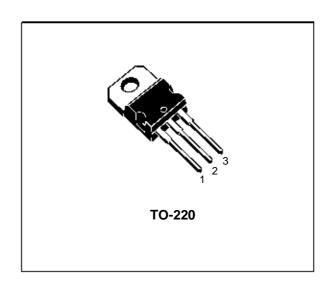
TIP31A/31B/31C TIP32A/32B/32C

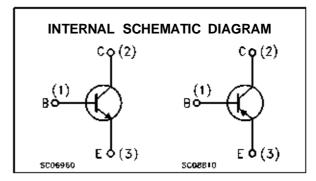
COMPLEMENTARY SILICON POWER TRANSISTORS

■ TIP31A, TIP31C, TIP32A, TIP32B, AND TIP32C ARE SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The TIP31A, TIP31B and TIP31C are silicon epitaxial-base NPN power transistors in Jedec TO-220 plastic package, intented for use in medium power linear and switching applications. The complementary PNP types are TIP32A, TIP32B and TIP32C.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter NPN			Unit		
			TIP31A	TIP31B	TIP31C	1
		PNP	TIP32A	TIP32B	TIP32C	
V _{CBO}	Collector-Base Voltage (I _E = 0)	60	80	100	V	
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		60	80	100	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)			V		
Ic	Collector Current			Α		
I _{CM}	Collector Peak Current			Α		
Ι _Β	Base Current			Α		
P _{tot}	Total Dissipation at T _{case} ≤ 25 °C			W		
	T _{amb} ≤ 25 °C			W		
T_{stg}	Storage Temperature			°C		
Tj	Max. Operating Junction Temperature		150			

For PNP types voltage and current values are negative.

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TIP31A/TIP31B/TIP31C/TIP32A/TIP32B/TIP32C

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3.12	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

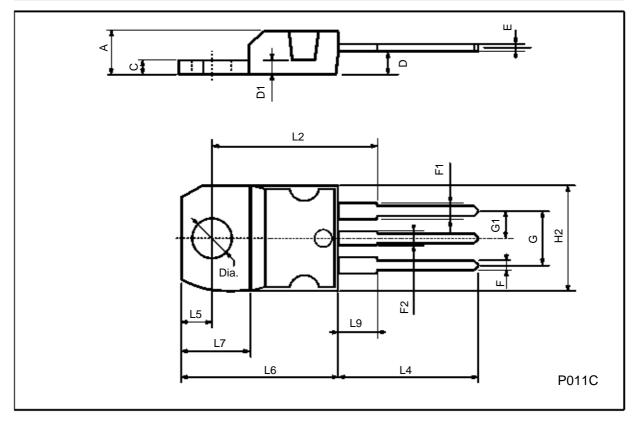
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _B = 0)	for TIP31A/32A V _{CE} = 30 V for TIP31B/31C/32B/32C V _{CB} = 60 V			0.3	mA mA
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	for TIP31A/32A			0.2 0.2 0.2	mA mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
VCEO(sus)*	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP31A/32A for TIP31B/32B for TIP31C/32C	60 80 100			V V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_C = 3 \text{ A}$ $I_B = 375 \text{ mA}$			1.2	V
V _{BE(on)} *	Base-Emitter Voltage	$I_C = 3 A$ $V_{CE} = 4 V$			1.8	V
h _{FE} *	DC Current Gain	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	25 10		50	
h _{fe}	Small Signal Current Gain	$\begin{split} I_{C} &= 0.5 \text{ A} & V_{CE} &= 10 \text{ V} \\ f &= 1 \text{ KHz} & \\ I_{C} &= 0.5 \text{ A} & V_{CE} &= 10 \text{ V} \\ f &= 1 \text{ MHz} & \end{split}$	20 3			

^{*} Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch			
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.40		4.60	0.173		0.181	
С	1.23		1.32	0.048		0.051	
D	2.40		2.72	0.094		0.107	
D1		1.27			0.050		
E	0.49		0.70	0.019		0.027	
F	0.61		0.88	0.024		0.034	
F1	1.14		1.70	0.044		0.067	
F2	1.14		1.70	0.044		0.067	
G	4.95		5.15	0.194		0.203	
G1	2.4		2.7	0.094		0.106	
H2	10.0		10.40	0.393		0.409	
L2		16.4			0.645		
L4	13.0		14.0	0.511		0.551	
L5	2.65		2.95	0.104		0.116	
L6	15.25		15.75	0.600		0.620	
L7	6.2		6.6	0.244		0.260	
L9	3.5		3.93	0.137		0.154	
DIA.	3.75		3.85	0.147		0.151	



TIP31A/TIP31B/TIP31C/TIP32A/TIP32B/TIP32C

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